

# SMD Schottky Barrier Diode

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## CDBS0130

**I<sub>o</sub> = 100mA**

**V<sub>R</sub> = 30 Volts**



### Features

Designed for mounting on small surface

Extremely thin package

Low stored charge

Majority carrier conduction

### Mechanical data

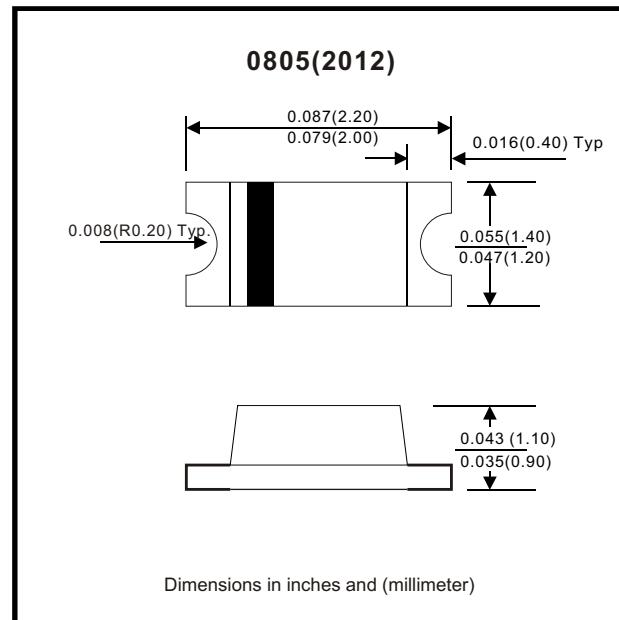
Case: 0805(2012)Standard package,  
molded plastic

Terminals: Solder plated, solderable per  
MIL-STD-750, method 2026

Polarity: Indicated by cathode band.

Mounting position: Any.

Weight: 0.0048 gram. ( approximately)



### Maximum Rating ( at T<sub>A</sub> = 25°C unless otherwise noted )

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V <sub>RRM</sub>			35	V
Reverse voltage		V <sub>R</sub>			30	V
Average forward current		I <sub>o</sub>			100	mA
Forward current , surge peak	8.3 ms single half sine-wave superimposed on rate load( JEDEC method )	I <sub>FSM</sub>		1000		mA
Power Dissipation		P <sub>D</sub>			250	mW
Storage temperature		T <sub>TG</sub>	-40		+125	°C
Junction temperature		T <sub>j</sub>	-40		+125	°C

### Electrical Characteristics ( at T<sub>A</sub> = 25°C unless otherwise noted )

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I <sub>F</sub> = 100 mA DC	V <sub>F</sub>			0.44	V
Reverse current	V <sub>R</sub> = 30 V	I <sub>R</sub>			30	uA
Capacitance between terminals	f = 1MHz, and 10 VDC reverse voltage	C <sub>T</sub>		10		pF

## RATING AND CHARACTERISTIC CURVES (CDBS0130)

Fig. 1 - Forward characteristics

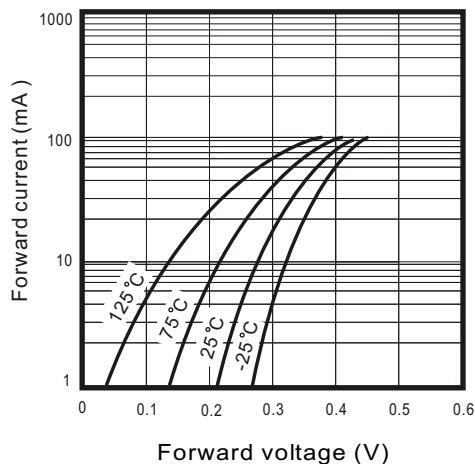


Fig. 2 - Reverse characteristics

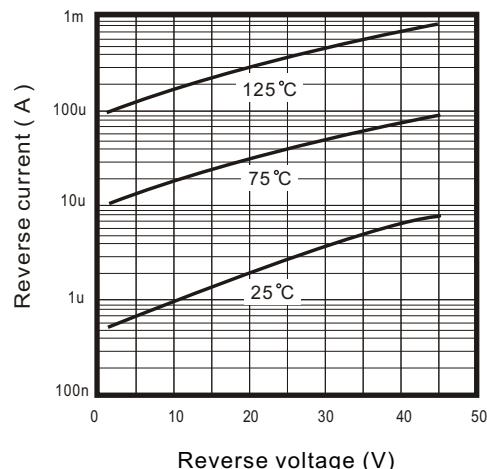


Fig. 3 - Capacitance between terminals characteristics

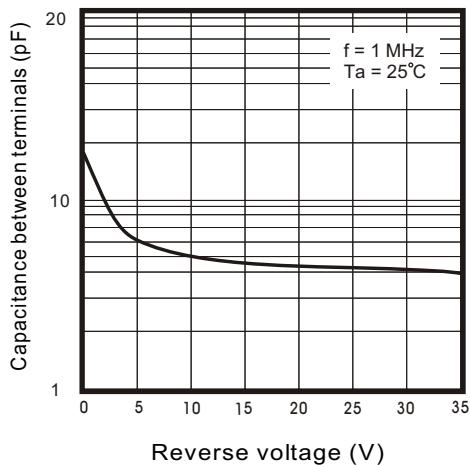


Fig. 4 - Current derating curve

